Elektronische Bauelemente

STT8205S

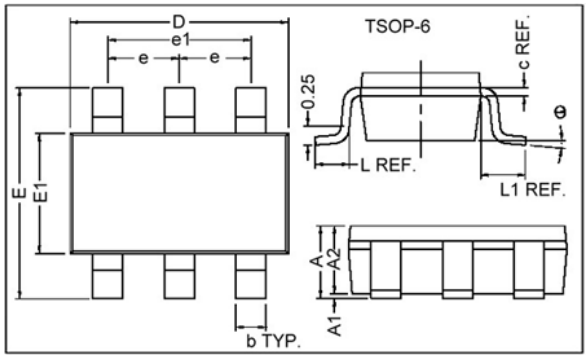
6 A, 20V, $R_{DS(ON)}$ 28mΩ

N-Channel Enhancement Mode Power Mos.FET

RoHS Compliant Product

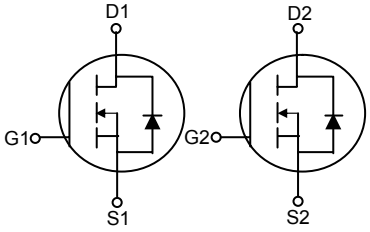
Description

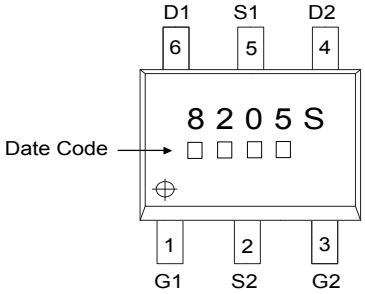
The STT8205S provide the designer with best combination of fast switching, low on-resistance and cost-effectiveness.
The TSSOP-6 package is universally used for all commercial-industrial surface mount applications.



Features

* Low Drive Current
* Low On-Resistance
* Capable of 2.5V Gate Drive





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	1.10 MAX.		L	0.45 REF.	
A1	0	0.10	L1	0.60 REF.	
A2	0.70	1.00	□	0°	10°
c	0.12 REF.		b	0.30	0.50
D	2.70	3.10	e	0.95 REF.	
E	2.60	3.00	e1	1.90 REF.	
E1	1.40	1.80			

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±8	V
Continuous Drain Current,[3] V_{GS}@4.5V	I_D@T_A=25°C	6	A
Continuous Drain Current,[3] V_{GS}@4.5V	I_D@T_A=70°C	4.8	A
Pulsed Drain Current[1]	I_{DM}	20	A
Total Power Dissipation	P_D@T_A=25°C	1.14	W
Linear Derating Factor		0.01	W/°C
Operating Junction and Storage Temperature Range	Tj, Tstg	-55~+150	°C

Thermal Data

Parameter	Symbol	Ratings	Unit
Thermal Resistance Junction-ambient[3] (Max)	Rthj-a	110	°C/W

Electrical Characteristics(Tj=25°C Unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Drain-Source Breakdown Voltage	BV_{DSS}	20	–	–	V	V_{GS}=0V, I_D= 250uA
Breakdown Voltage Temp. Coefficient	$\triangle BV_{DS}/\triangle Tj$	–	0.03	–	V/ °C	Reference to 25°C, I_D= 1mA
Gate Threshold Voltage	$V_{GS(th)}$	0.5	–	1.5	V	V_{DS}=V_{GS}, I_D=250uA
Gate-Source Leakage Current	I_{GSS}	–	–	± 100	uA	V_{GS}=± 8V
Drain-Source Leakage Current (Tj=25°C)	I_{DSS}	–	–	1	uA	V_{DS}=20V, V_{GS}=0
Drain-Source Leakage Current (Tj=70°C)		–	–	25	uA	V_{DS}= 16V, V_{GS}=0
Static Drain-Source On-Resistance[2]	$R_{DS(ON)}$	–	–	28	mΩ	V_{GS}=4.5 V, I_D=6A
		–	–	38		V_{GS}=2.5V, I_D=5.2A
Total Gate Charge[2]	Qg	–	23	–	nC	I_D=6 A V_{DS}=20V V_{GS}=5V
Gate-Source Charge	Qgs	–	4.5	–		
Gate-Drain ("Miller") Charge	Qgd	–	7	–		
Turn-on Delay Time[2]	$Td_{(ON)}$	–	30	–	nS	V_{DD}= 10V I_D= 1 A V_{GS}=5 V R_G=6 Ω R_D=10 Ω
Rise Time	Tr	–	70	–		
Turn-off Delay Time	$Td_{(Off)}$	–	40	–		
Fall Time	T_f	–	65	–		
Input Capacitance	Ciss	–	1035	–	pF	V_{GS}=0V V_{DS}=20V f=1.0MHz
Output Capacitance	Coss	–	320	–		
Reverse Transfer Capacitance	Crss	–	150	–		
Forward Transconductance	Gfs	–	20	–	S	V_{DS}=10V, I_D=6 A

Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Forward On Voltage[2]	V_{SD}	–	–	1.2	V	I_S=1.7 A, V_{GS}=0V.

Notes: 1.Pulse width limited by Max. junction temperature.

2.Pulse width ≦300us, dutycycle ≦2%.

3.Surface mounted on 1 in^{2}copper pad of FR4 board; 180 °C/W when mounted on min. copper pad.

Characteristics Curve

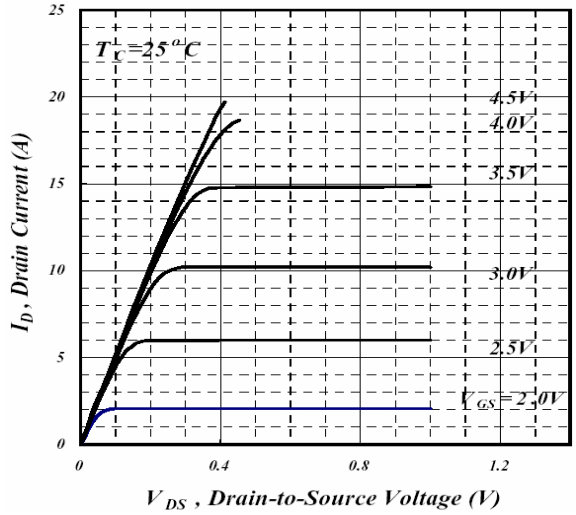


Fig 1. Typical Output Characteristics

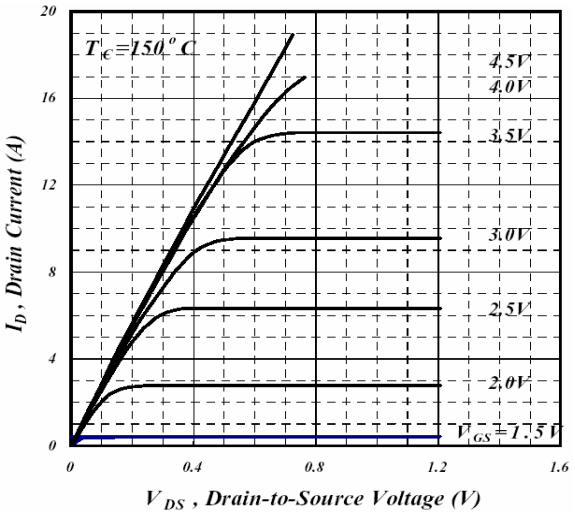


Fig 2. Typical Output Characteristics

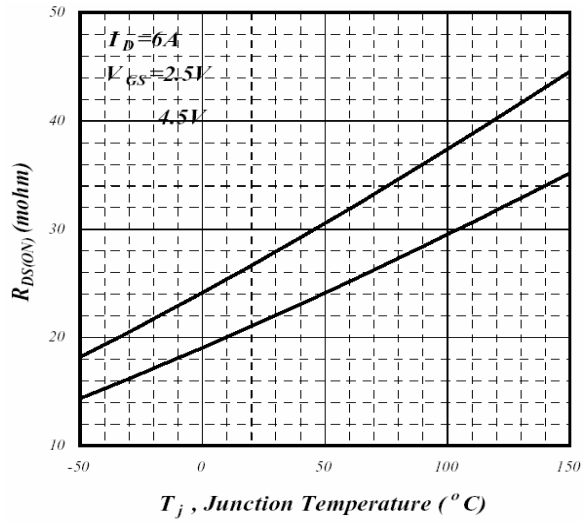


Fig 3. R_{DSON} v.s. Junction Temperature

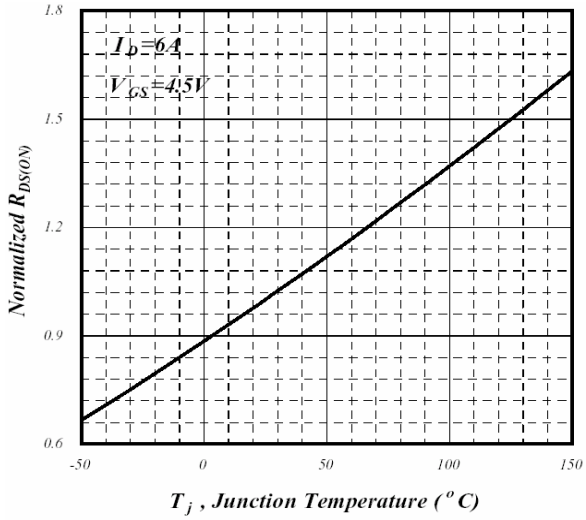


Fig 4. Normalized On-Resistance v.s. Junction Temperature

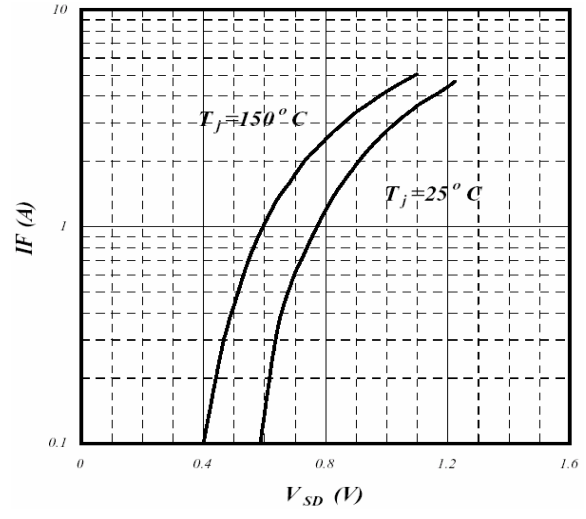


Fig 5. Forward Characteristics of Reverse Diode

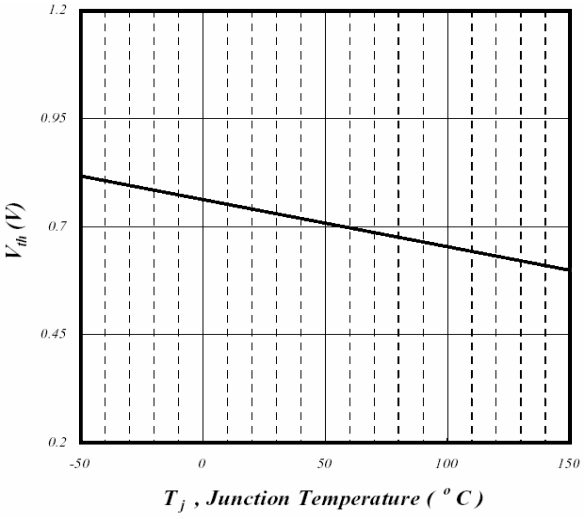


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

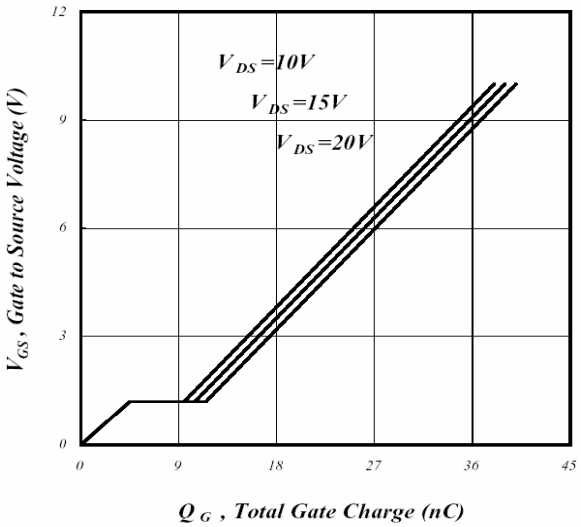


Fig 7. Gate Charge Characteristics

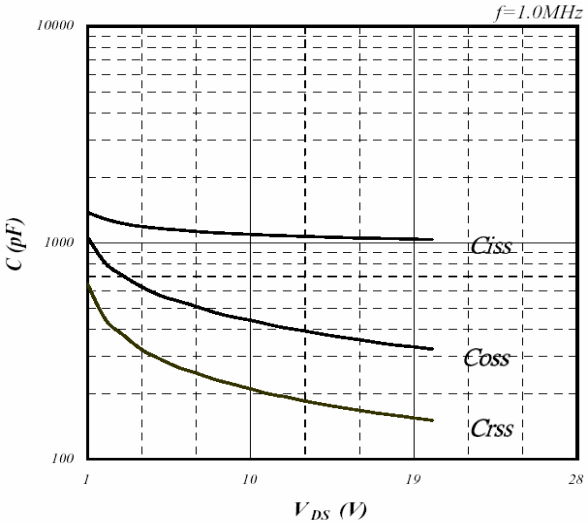


Fig 8. Typical Capacitance Characteristics

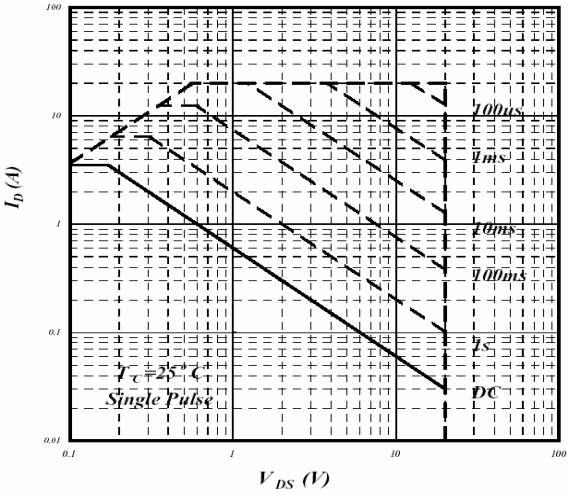


Fig 9. Maximum Safe Operating Area

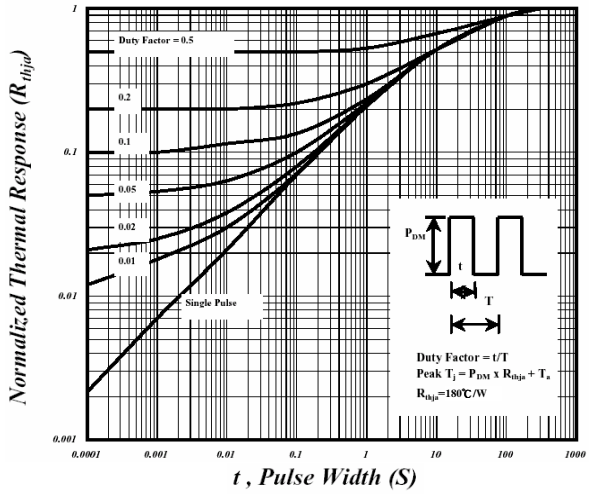


Fig 10. Effective Transient Thermal Impedance

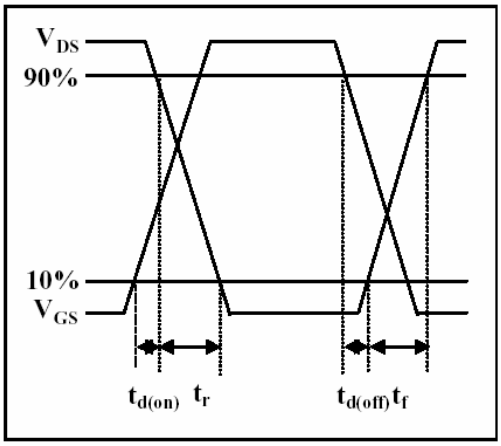


Fig 11. Switching Time Waveform

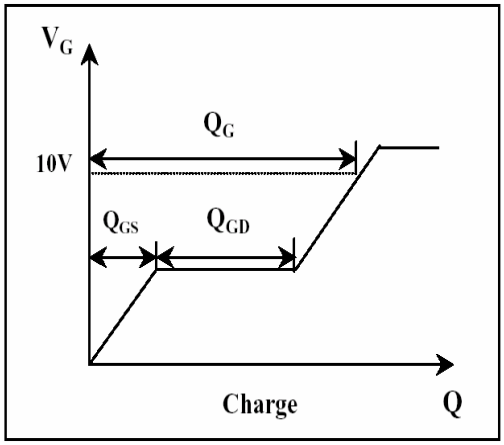


Fig 12. Gate Charge Waveform